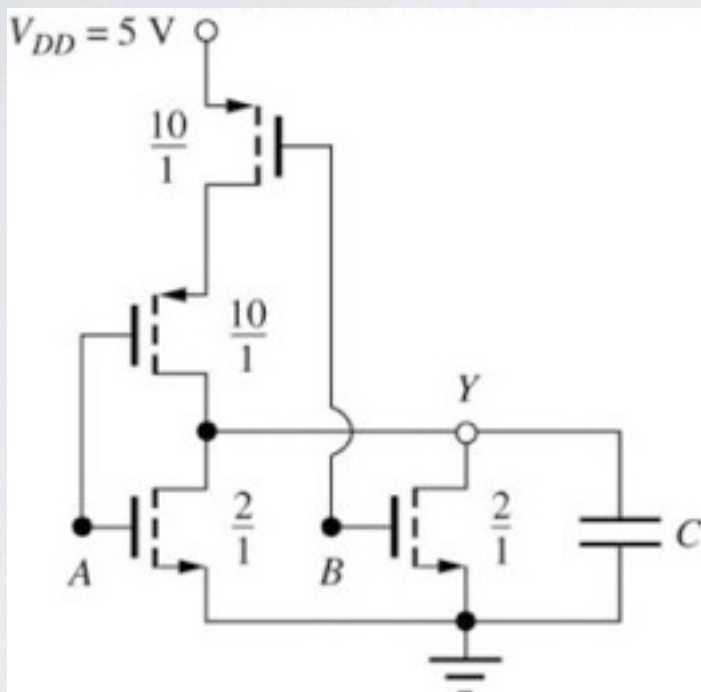


# COMPLEX CMOS LOGIC DESIGN

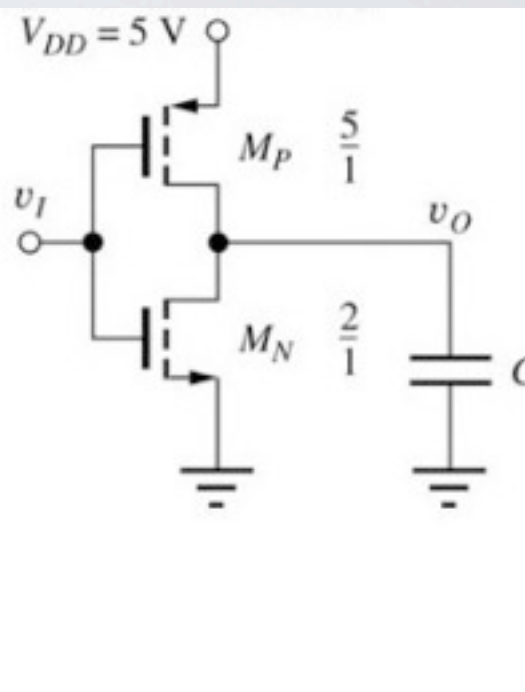
INEL 4207 Digital Electronics

M.Toledo - Spring 2012

# CMOS NOR GATE



CMOS NOR gate  
implementation



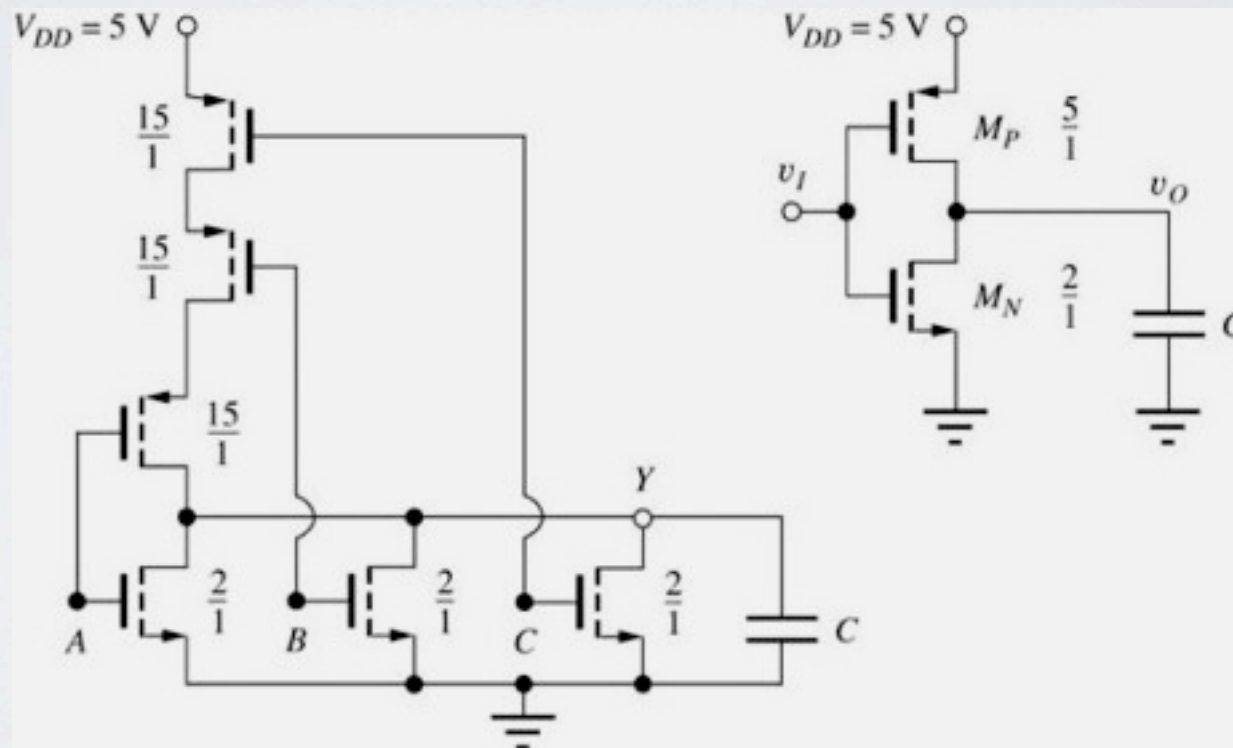
Reference Inverter

# CMOS NOR GATE SIZING

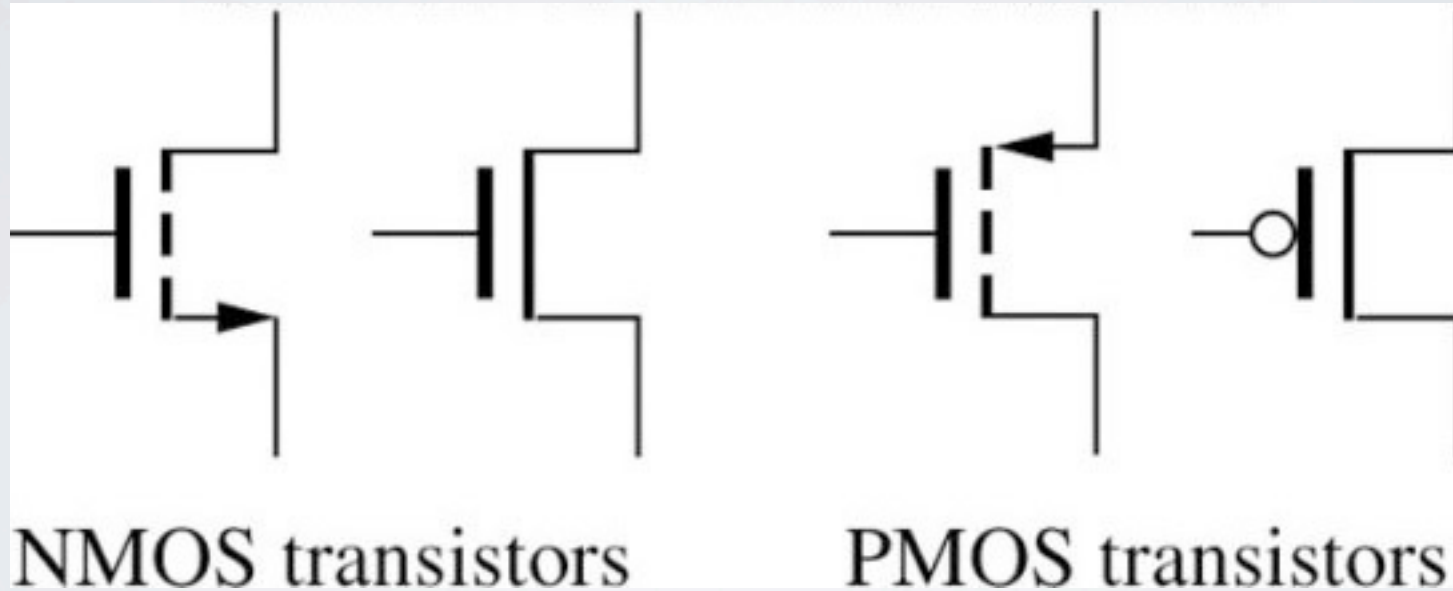
- Size transistors to keep delay times the same as the reference inverter.
- the on-resistance on the PMOS branch of the NOR gate must be the same as the reference inverter
- For a two-input NOR gate, the  $(W/L)_p$  must be made twice as large

# THREE-INPUT NOR GATE LAYOUT

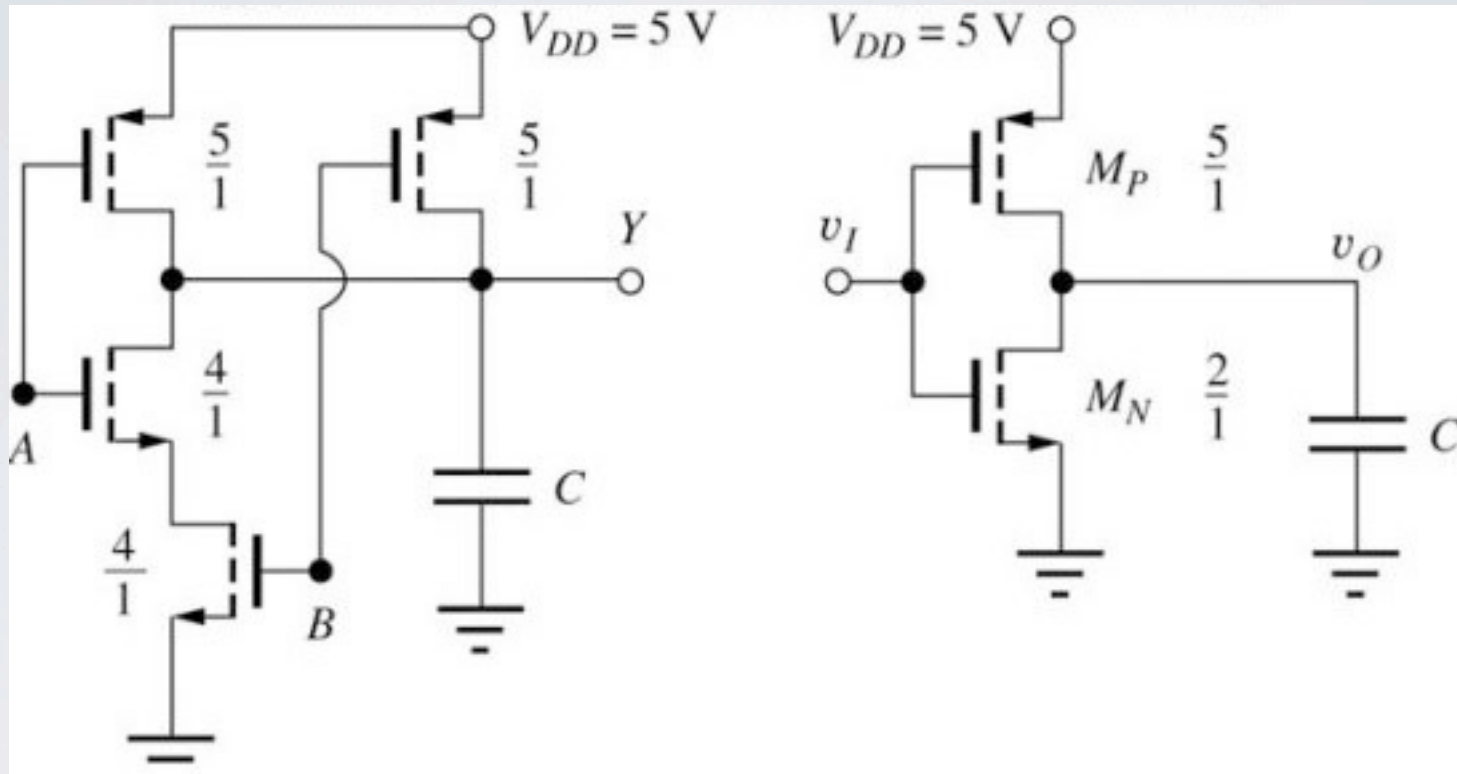
- It is possible to extend this same design technique to create multiple input NOR gates



# SHORTHAND NOTATION FOR NMOS AND PMOS



# CMOS NAND GATES



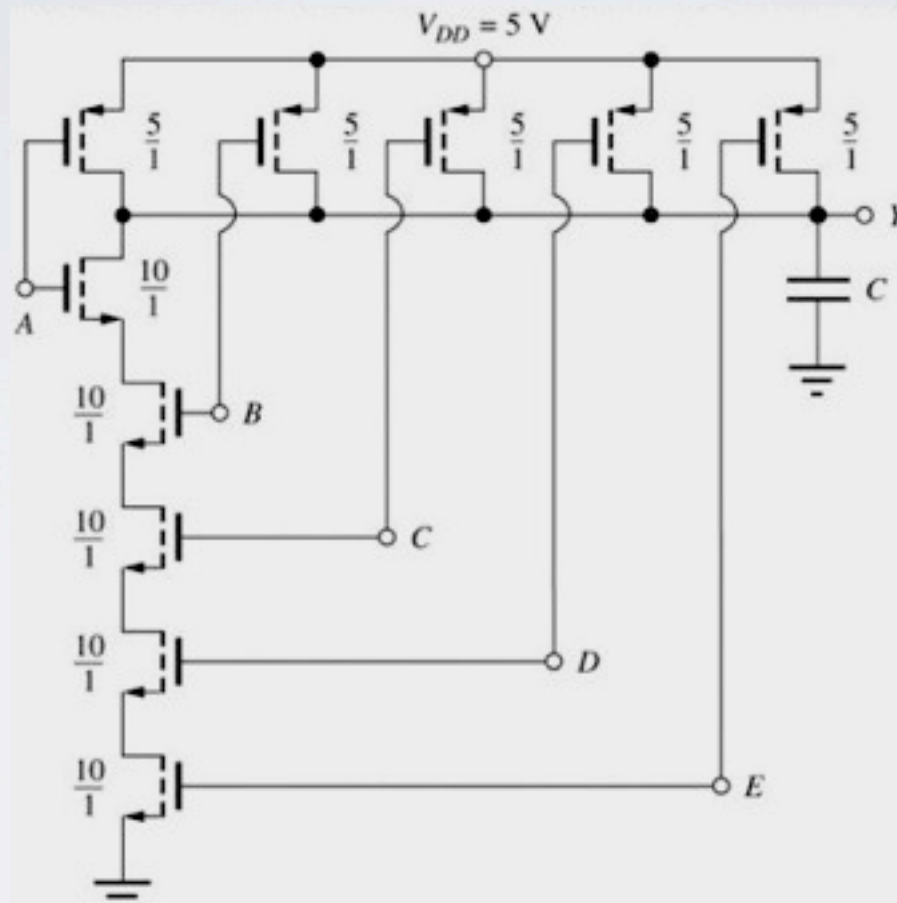
CMOS NAND gate  
implementation

Reference Inverter

# CMOS NAND GATES SIZING

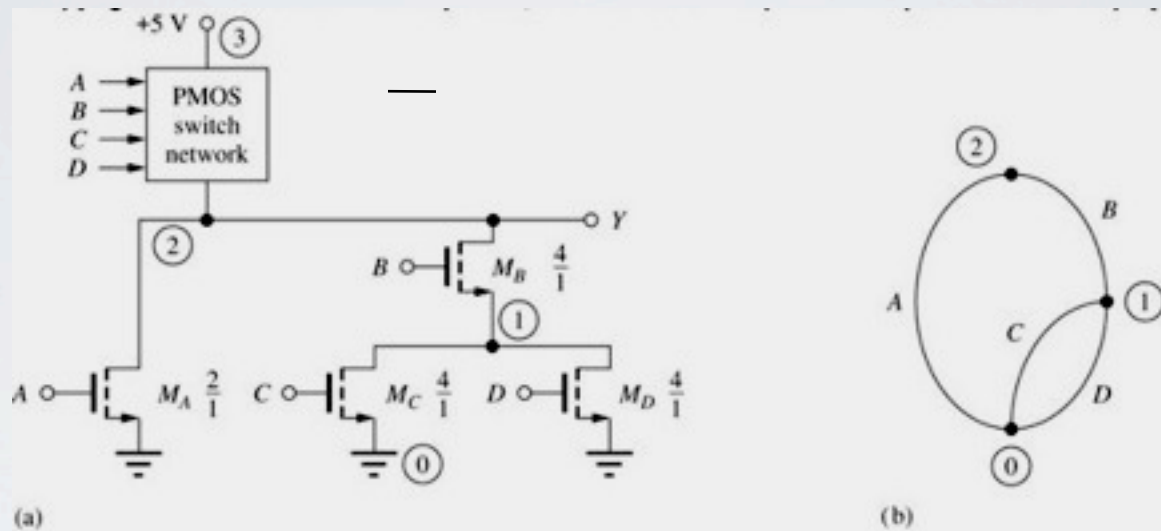
- The same rules apply for sizing the NAND gate as the did for the NOR gate, except for now the NMOS transistors are in series
- The  $(W/L)_N$  will be twice the size of the reference inverter's NMOS

# MULTI-INPUT CMOS NAND GATES



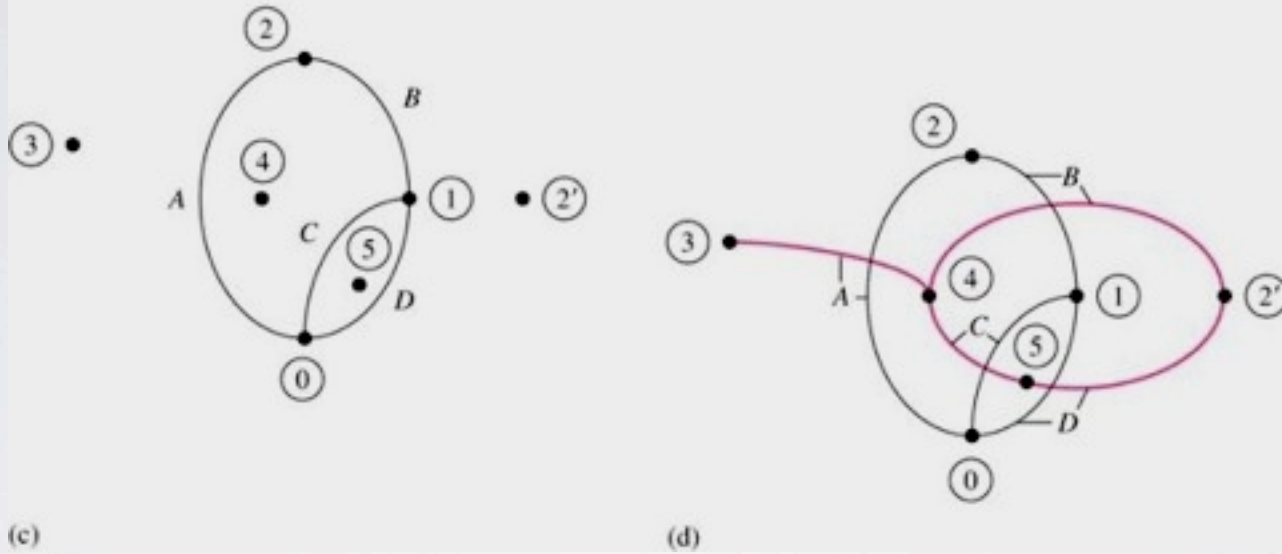


# COMPLEX CMOS LOGIC GATE DESIGN EXAMPLE



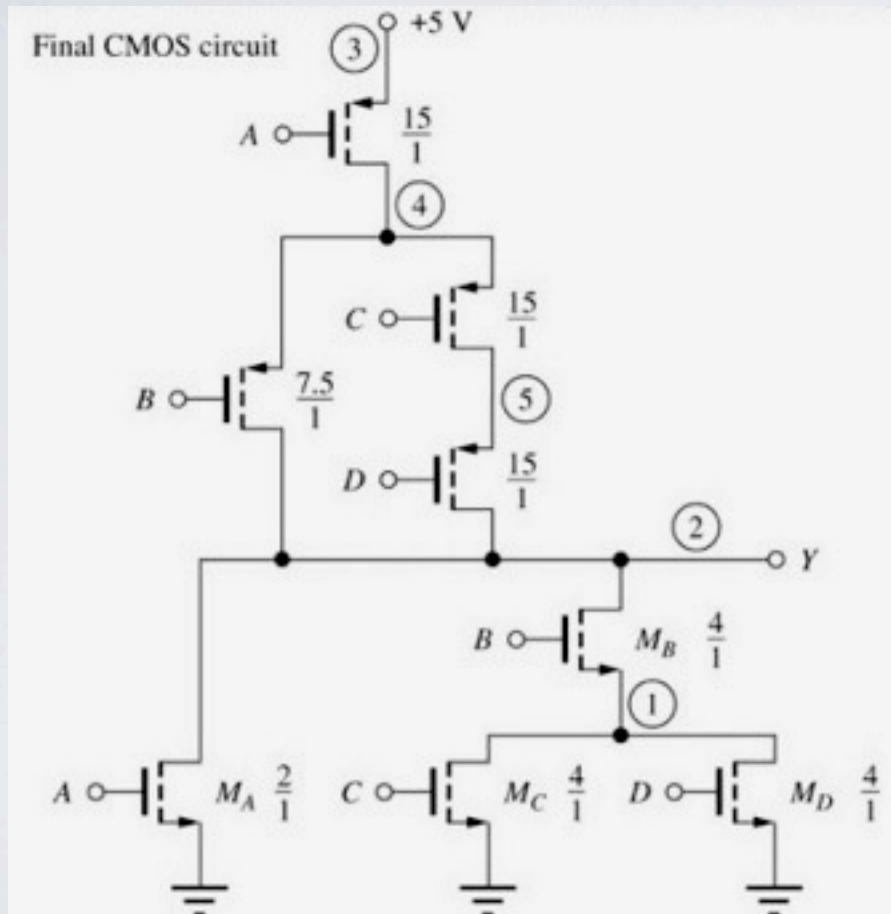
- Design a CMOS logic gate for  $(W/L)_{p,ref} = 5/1$  and for  $(W/L)_{n,ref} = 2/1$  that exhibits the function:  $Y' = A + BC + BD$
- By inspection (knowing Y), the NMOS branch of the gate can be drawn as the following with the corresponding graph, while considering the longest path for sizing purposes:

# COMPLEX CMOS LOGIC GATE DESIGN EXAMPLE



- By placing nodes in the interior of each arc, plus two more outside the graph for  $V_{DD}$  (3) and the complementary output (2'), the PMOS branch can be realized as shown on the left figure
- Connect all of the nodes in the manner shown in the right figure, and the NMOS arc that PMOS arc intersects have the same inputs

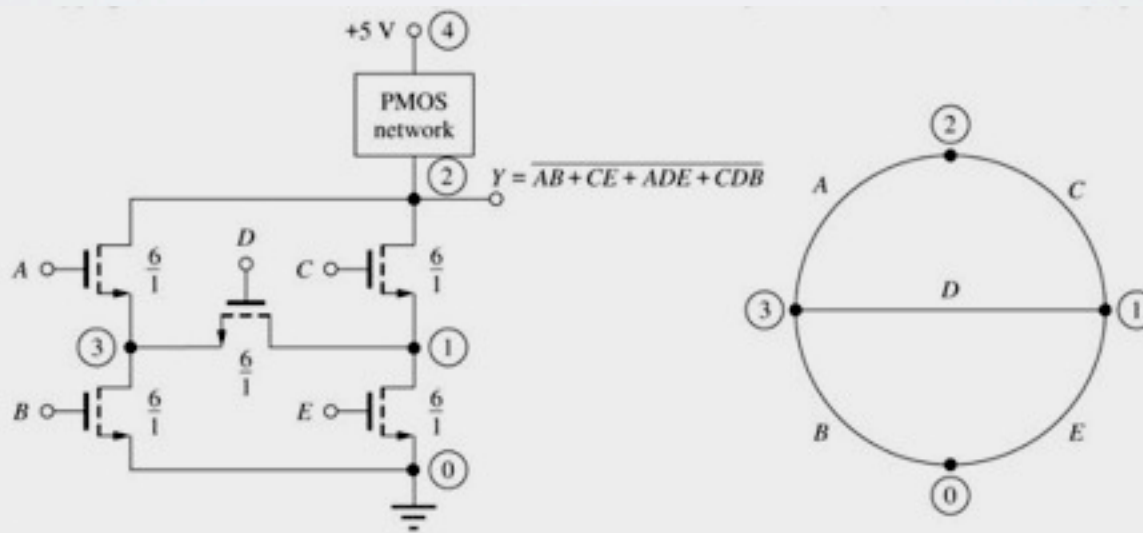
# COMPLEX CMOS LOGIC GATE DESIGN EXAMPLE



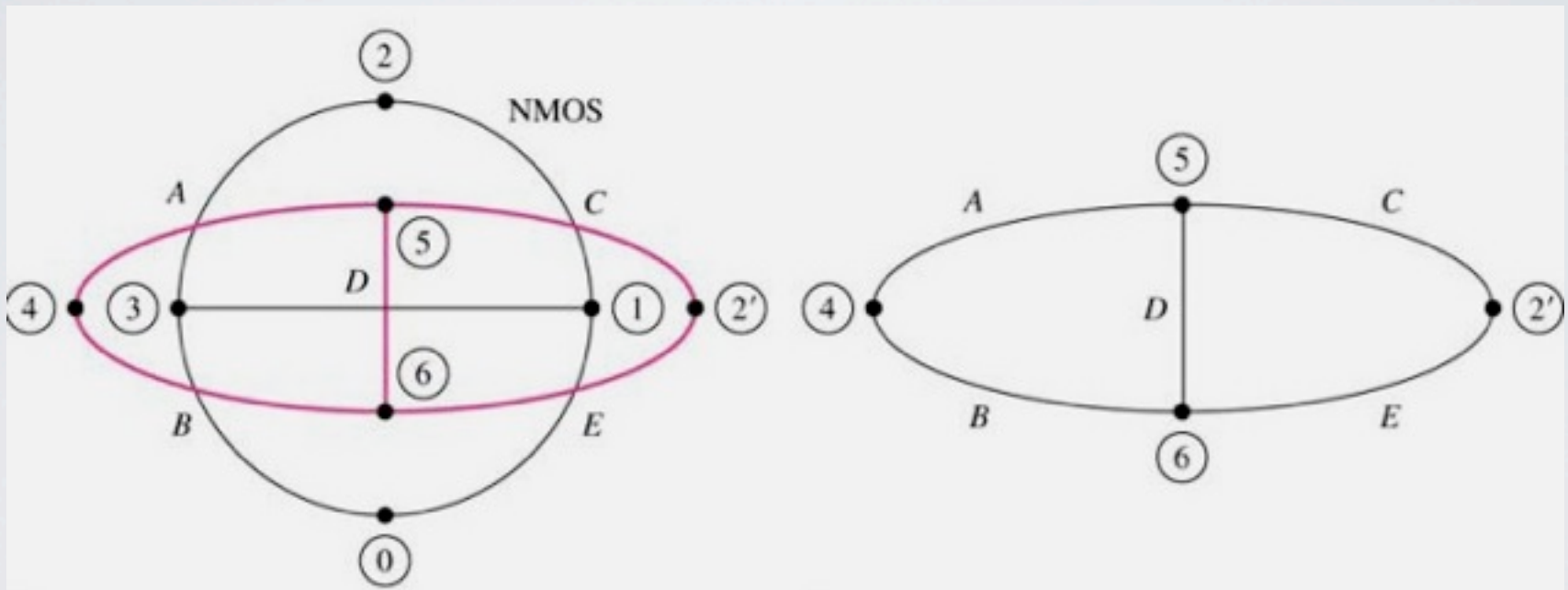
- From the PMOS graph, the PMOS branch can now be drawn for the final CMOS logic gate while once again considering the longest PMOS path for sizing

# COMPLEX CMOS GATE WITH A BRIDGING

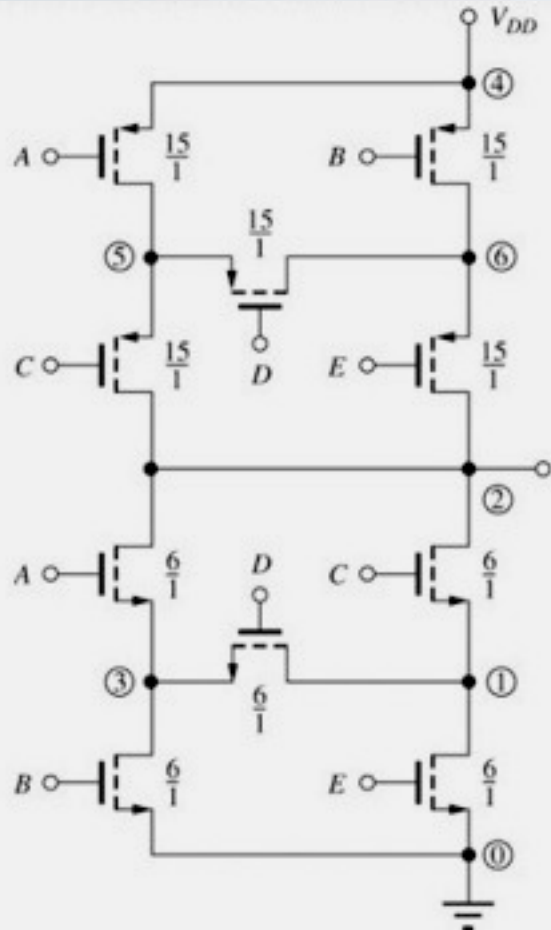
- Design a CMOS gate that implements the following logic function using the same reference inverter sizes as the previous example:
  - $Y = AB + CE + ADE + CDB$
- The NMOS branch can be realized in the following manner using bridging NMOS D to implement Y. The corresponding NMOS graph is shown to the right.



# COMPLEX CMOS GATE WITH A BRIDGING



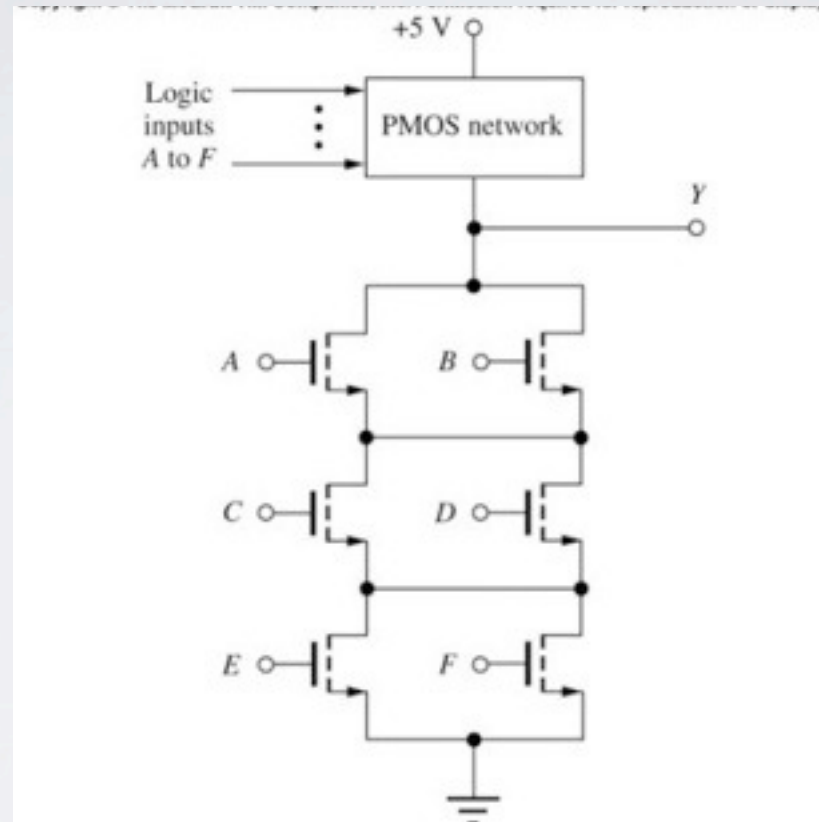
# COMPLEX CMOS GATE WITH A BRIDGING



By using the PMOS graph the PMOS branch can now be realized as the one shown on the left.

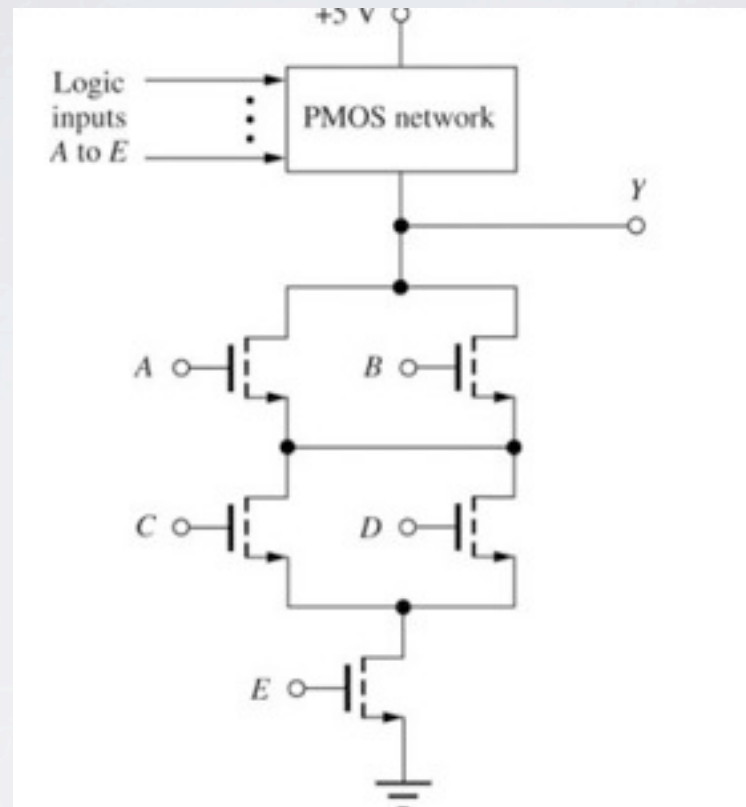
The longest path was used to select sizing.

Find Pull-up Network (PUN)



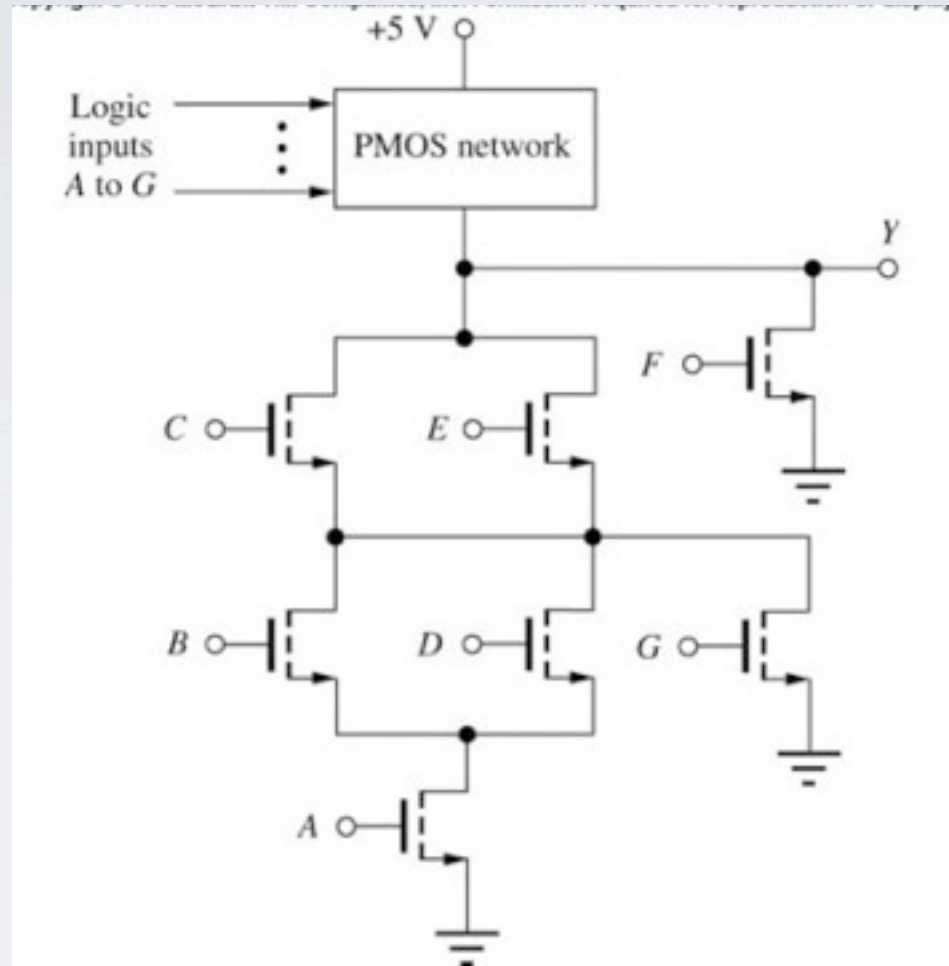


# PUN?





# PUN?



- Design a CMOS logic gate based on the reference inverter to implement the following function:

$$Y = (ABC + DE)'$$

Select transistor sizes to obtain propagation times similar to those of the reference inverter.

- Design CMOS L.G. to implement

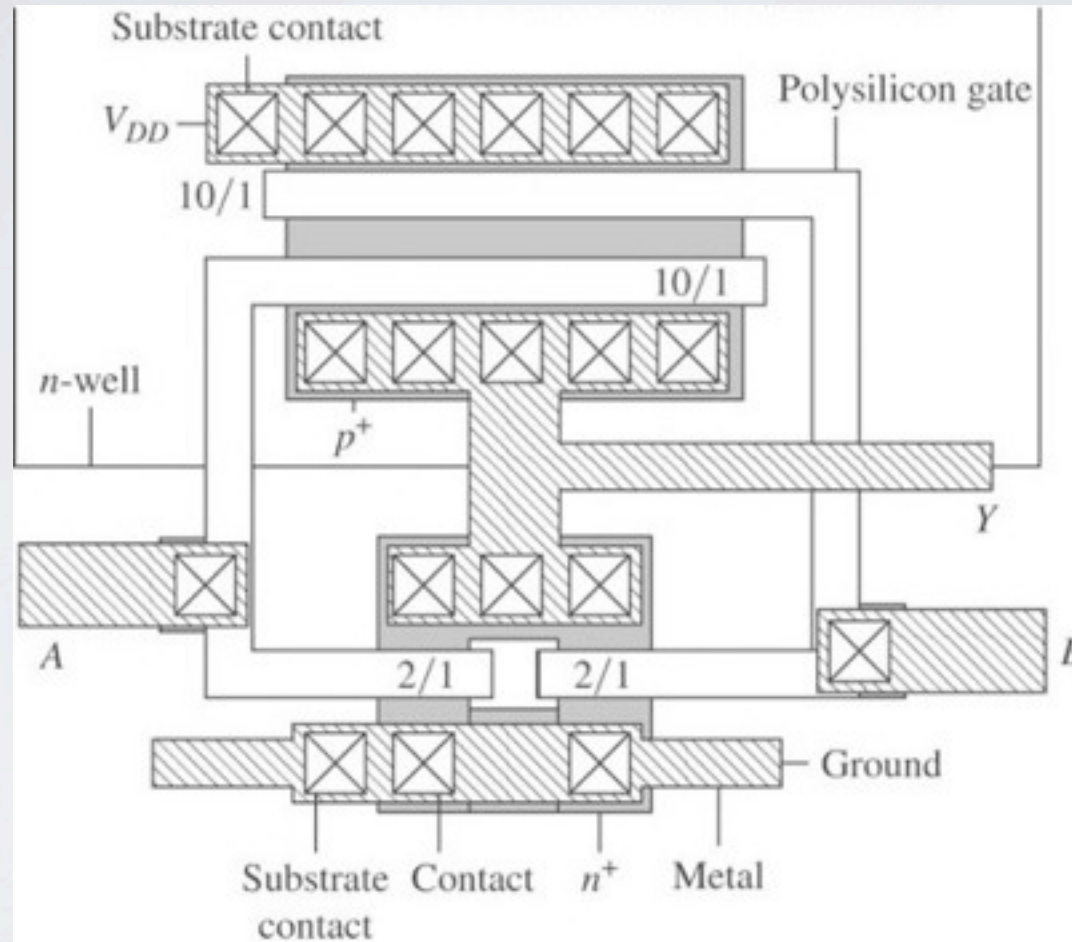
$$Y=[A(B+C(D+E))]'$$

Select sizes to obtain same  $t_p$  as in reference inverter.

# CMOS NOR GATE BODY EFFECT

- Since the bottom PMOS body contact is not connected to its source, its threshold voltage changes as  $V_{SB}$  changes during switching
- Once  $v_O = V_H$  is reached, the bottom PMOS is not affected by body effect, thus the total on-resistance of the PMOS branch is the same
- However, the rise time is slowed down due to  $|V_{TP}|$  being a function of time

# TWO-INPUT NOR GATE LAYOUT



# MINIMUM SIZE GATE DESIGN AND PERFORMANCE

- With CMOS technology, there is a area/delay tradeoff that needs to be considered
- If minimum feature sized are used for both devices, then the  $\tau_{PLH}$  will be decreased compared to the symmetrical reference inverter

# MINIMUM SIZE COMPLEX GATE AND LAYOUT

